

## ABSTRACT:

A method of manufacturing an electronic device, a semiconductor device in particular but not exclusively, which method comprises the steps of:

- applying a semiconductor substrate (1) which is provided with a conductor (3,4,5) at a surface (2), the conductor (3,4,5) having a top surface portion (6) and sidewall portions (7),
- 5 of which at least the top surface portion (6) is provided with an etch stop layer (12) comprising silicon carbide,
- applying a dielectric layer (13),
- etching a via (14,15,16) in the dielectric layer (13) over the conductor (3,4,5), and stopping on the etch stop layer (12) to create an exposed part of the etch stop layer (12),
- 10 - removing the exposed part of the etch stop layer (12) inside the via (14,15,16) from at least the top surface portion (6) of the conductor (3,4,5),
- filling the via (14,15,16) with a conductive material (18).

15 Fig. 4